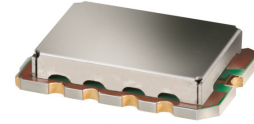# Low Noise Amplifier   TAMP-1521GLN+

50Ω   1380 to 1520 MHz

The Big Deal:

- Ultra Low Noise Figure, 0.75 dB typ.
- High IP3, 27 dBm typ.
- High Gain, 35 dB typ.
- Integrated Bias Matching and Stability Circuits

Click here for **data sheet**

Pricing: **$14.95** (QTY 5-49)

Product Overview:

The TAMP-1521GLN+ (RoHS compliant) utilizes advanced E-PHEMT technology in a 2-stage Low Noise Amplifier design built into a shielded case (size: .591"x.394"x.118"). The drop-in module offers ultra low Noise Figure and High Gain with good input and output return loss over the entire frequency range and without the need of external matching components.

Key Features

Feature	Advantages
Ultra Low NF	With only 0.75 dB NF, the TAMP-1521GLN+ enables greater sensitivity for receiver applications. It includes all matching and stability circuits making this Drop-in LNA module a turn-key solution for ensuring system sensitivity in demanding applications.
High IP3	At +27 dBm IP3, in combination with its low noise performance, the TAMP-1521GLN+ can improve a systems' spur-free dynamic range which is often the critical driver in many receiver applications.
Very flat, High Gain	With gain of 35 dB and flatness of ± 0.7 dB, this amplifier can insulate a receiver NF from component losses or NF of the 2nd stage amplifier following the TAMP-1521GLN+
Output Power, +14 dBm	Provides a good safety margin against damage or saturation from unwanted high power RF signals present at the input to a receiver.
Well Matched input/ output ports	With typical return loss of 18dB at the input and output ports, the TAMP-1521GLN+ can be used in cascade with many 50 Ohm components and maintain minimal interaction or reflections.
Drop-in Module	Eliminates the need for designers to optimize low noise transistor bias and matching circuitry. The TAMP-1521GLN+ provides the outstanding combined performance and does not require any external elements. The case PCB area is smaller than most LNA transistor designs with external circuitry
Metal Case	Provides a protective enclosure improving handling robustness in addition to shielding the sensitive high gain devices from close by circuitry
Unconditionally stable	No adverse effects due to loading of the input and output ports avoiding potential instability which can be a critical requirement when integrating high gain, high frequency devices on an open PCB assembly